

Description

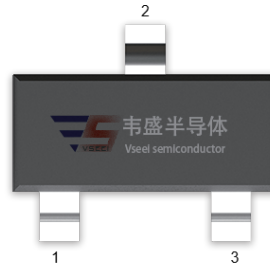
The VSM60P03Y uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This device is well suited for use as a load switch or in PWM applications.

General Features

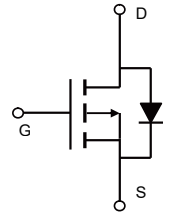
- $V_{DS} = -60V, I_D = -3A$
 $R_{DS(ON)} < 84m\Omega @ V_{GS} = -10V$
- High density cell design for ultra low $R_{DS(ON)}$
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

Application

- Load switch
- PWM application



SOT-23



Schematic

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VSM60P03Y	VSM60P03Y-S2	SOT-23	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-3	A
Pulsed Drain Current (Note 1)	I_{DM}	-16	A
Maximum Power Dissipation	P_D	1.5	W
Single pulse avalanche energy (Note 5)	E_{AS}	72	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	83.3	$^\circ C/W$
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Electrical Characteristics ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = -250\mu A$	-60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -60V, V_{GS} = 0V$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	± 100	nA
On Characteristics (Note 3)						

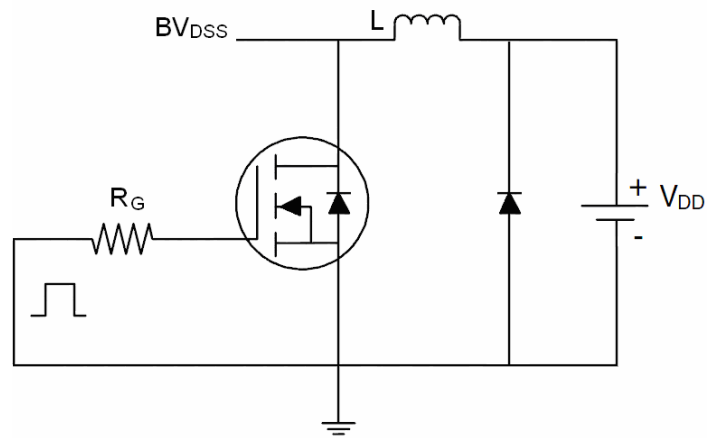
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.0	-1.8	-2.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-3A$	-	62	84	mΩ
Forward Transconductance	g_{FS}	$V_{DS}=-5V, I_D=-3A$	-	8	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{ISS}	$V_{DS}=-30V, V_{GS}=0V,$ $F=1.0MHz$	-	799	-	PF
Output Capacitance	C_{OSS}		-	50	-	PF
Reverse Transfer Capacitance	C_{RSS}		-	42	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-30V, R_L=10\Omega,$ $V_{GS}=-10V, R_G=3\Omega$	-	7	-	nS
Turn-on Rise Time	t_r		-	4	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	28	-	nS
Turn-Off Fall Time	t_f		-	6	-	nS
Total Gate Charge	Q_g	$V_{DS}=-30, I_D=-3A,$ $V_{GS}=-10V$	-	19	-	nC
Gate-Source Charge	Q_{gs}		-	3.4	-	nC
Gate-Drain Charge	Q_{gd}		-	4.4	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=-3A$	-		-1.2	V
Diode Forward Current (Note 2)	I_S		-	-	-3	A
Reverse Recovery Time	t_{rr}	$T_J = 25^{\circ}C, I_F = - 3A$ $di/dt = -100A/\mu s$ (Note3)	-	24		nS
Reverse Recovery Charge	Q_{rr}		-	29		nC

Notes:

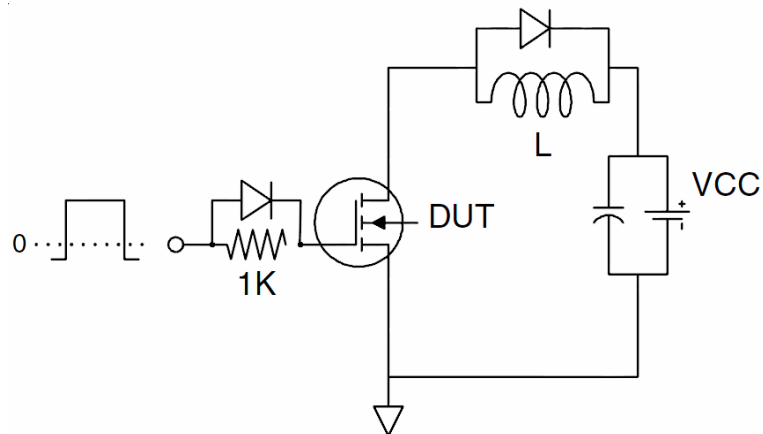
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition : $T_J=25^\circ C, V_{DD}=-20V, V_G=-10V, L=0.5mH, R_g=25\Omega$

Test Circuit

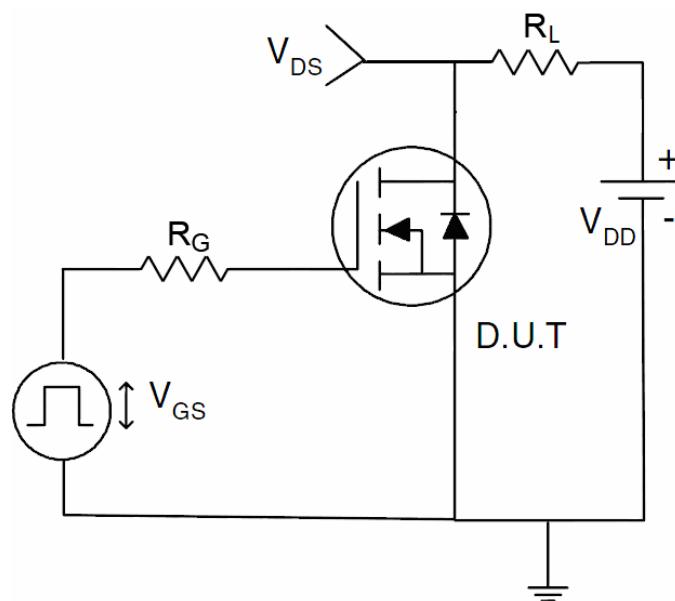
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

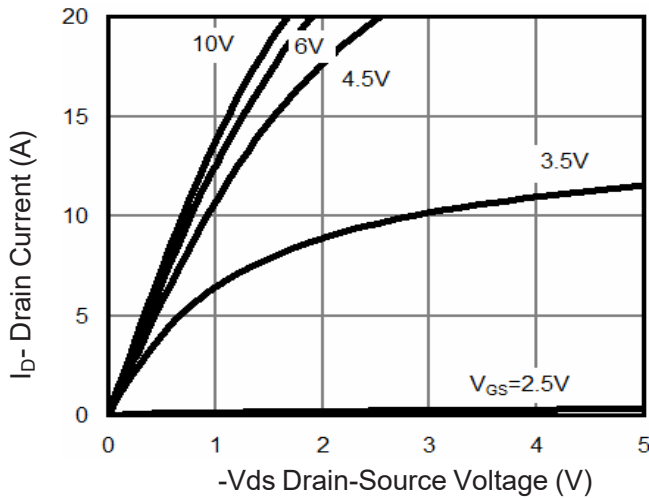


Figure 1 Output Characteristics

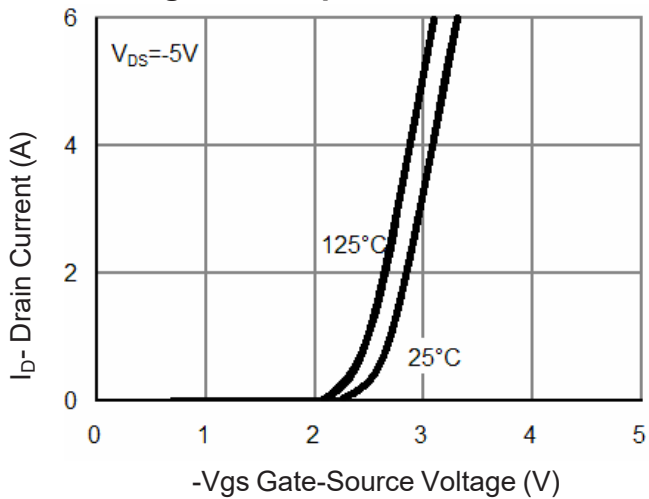


Figure 2 Transfer Characteristics

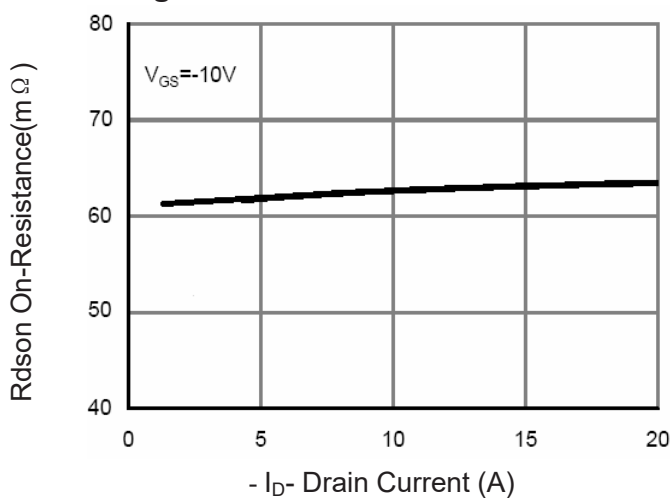


Figure 3 $R_{DS(on)}$ - Drain Current

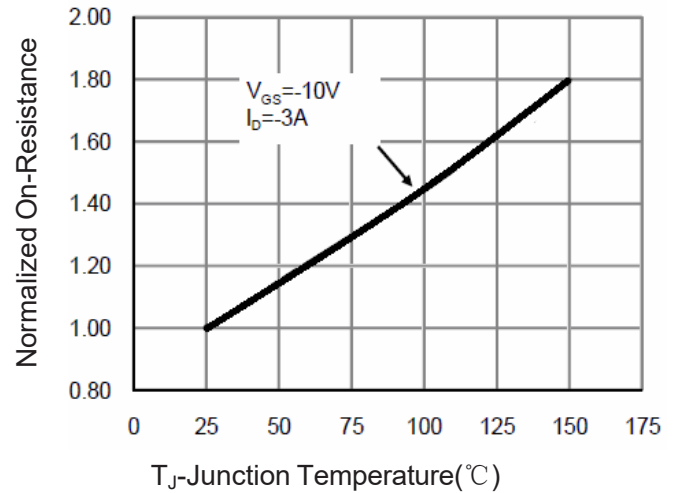


Figure 4 $R_{DS(on)}$ -Junction Temperature

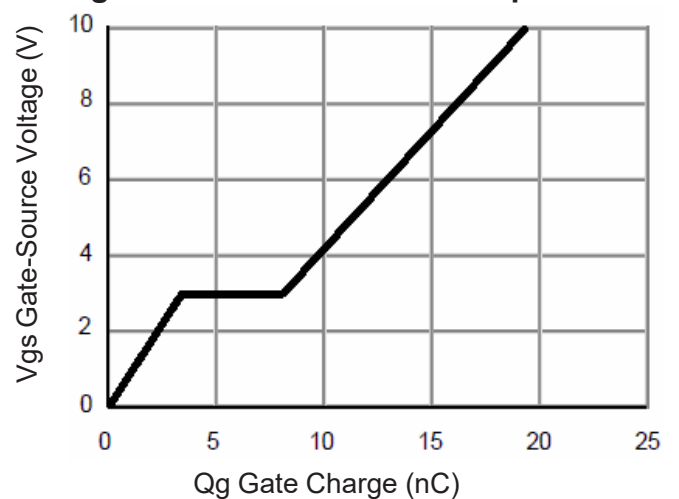


Figure 5 Gate Charge

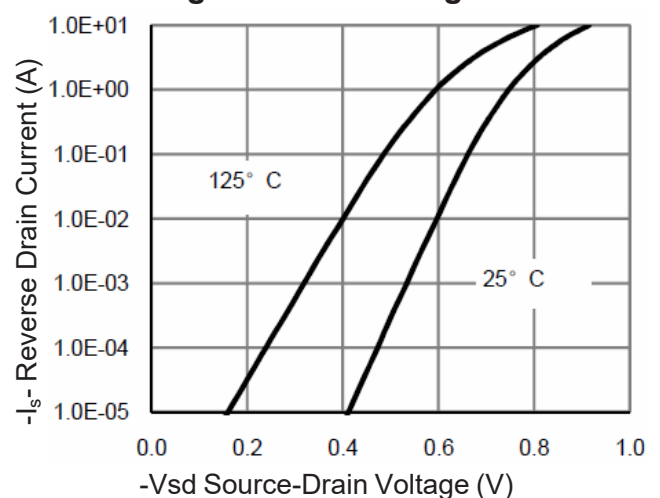
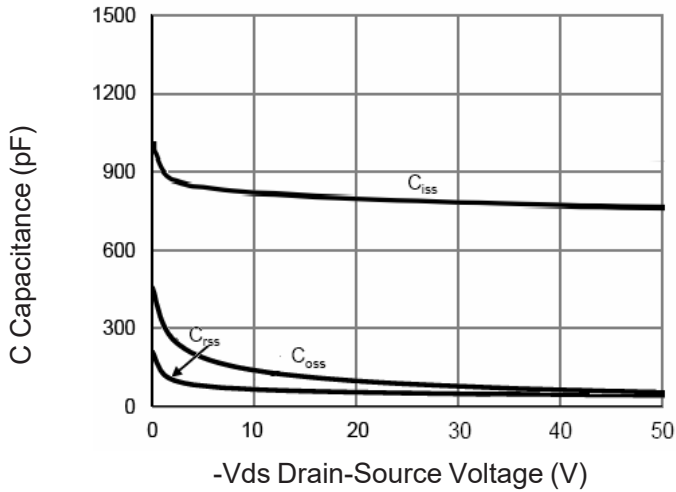
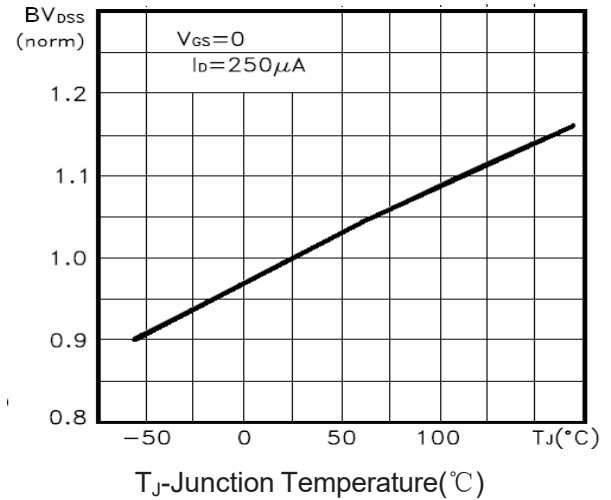
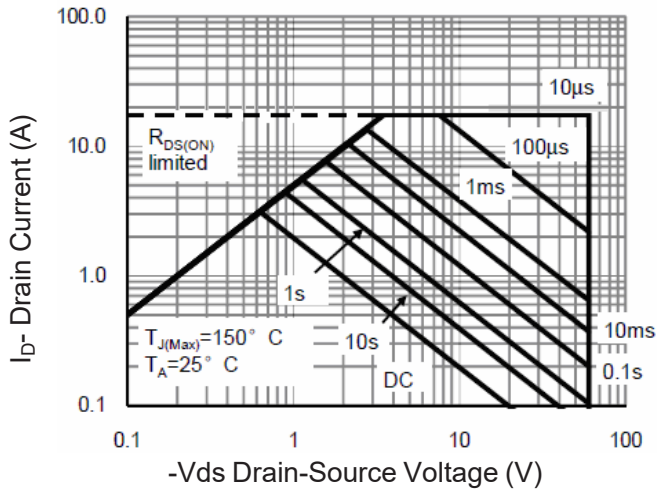
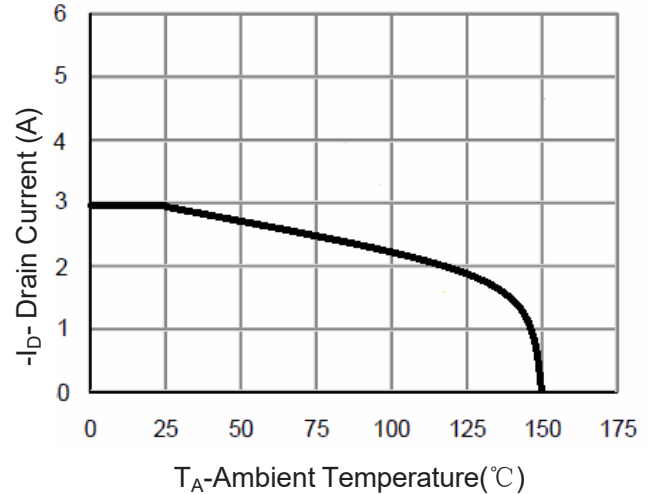
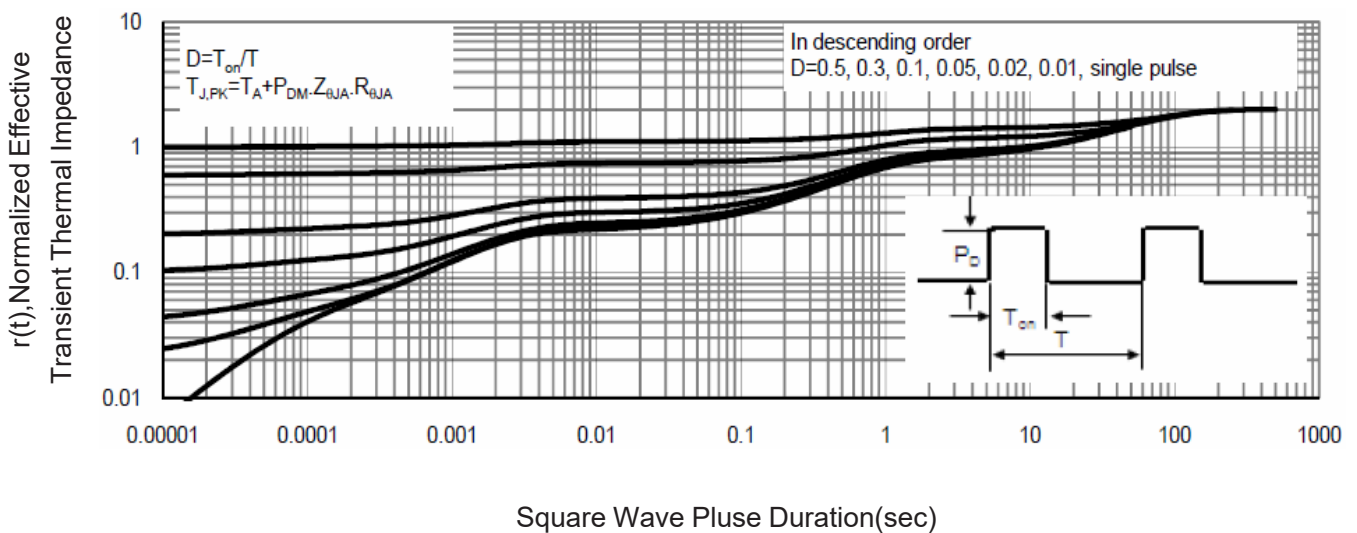


Figure 6 Source- Drain Diode Forward


Figure 7 Capacitance vs Vds

Figure 9 BV_{DSS} vs Junction Temperature

Figure 8 Safe Operation Area

Figure 10 I_D Current De-rating

Figure 11 Normalized Maximum Transient Thermal Impedance